

ABSTRACT

A multiple layered wafer structure having, on a semiconductor substrate, a first dielectric layer, a single crystal semiconductor layer formed on the dielectric layer, a semiconductor nano-crystal layer formed on the single crystal semiconductor layer, and a second dielectric layer formed on the semiconductor nano-crystal layer. A laser is irradiated from the side of the second dielectric layer, to thereby separate the second dielectric layer from the others of the multiple layered wafer structure.